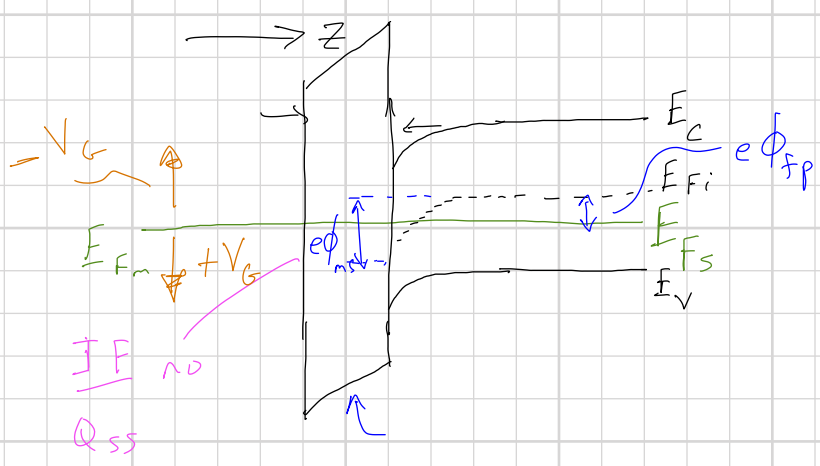


Lecture #13

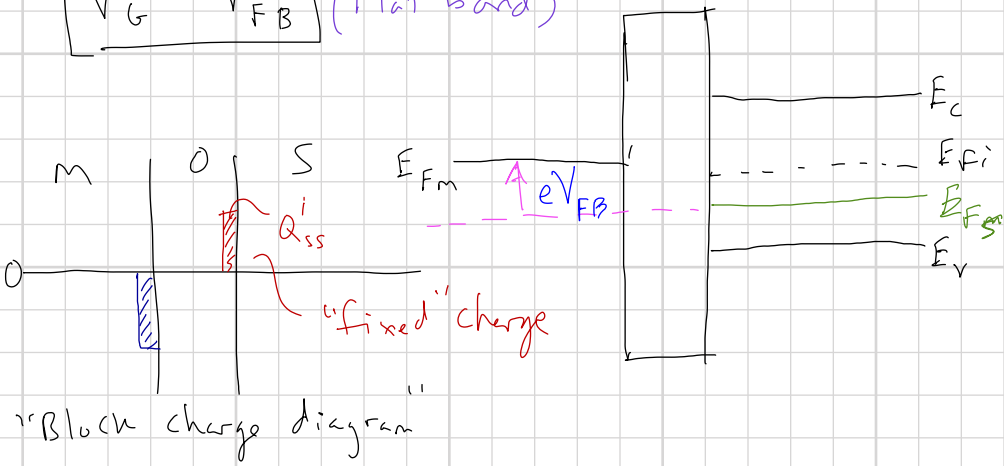
MOS Capacitor : C-V

Function of MOS-C (p-type)

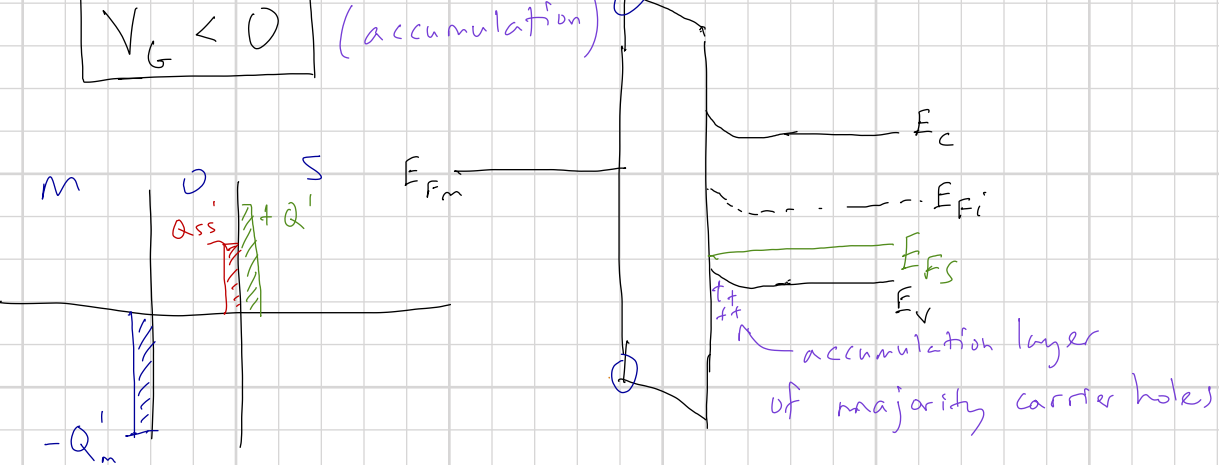
$V_G = 0V$



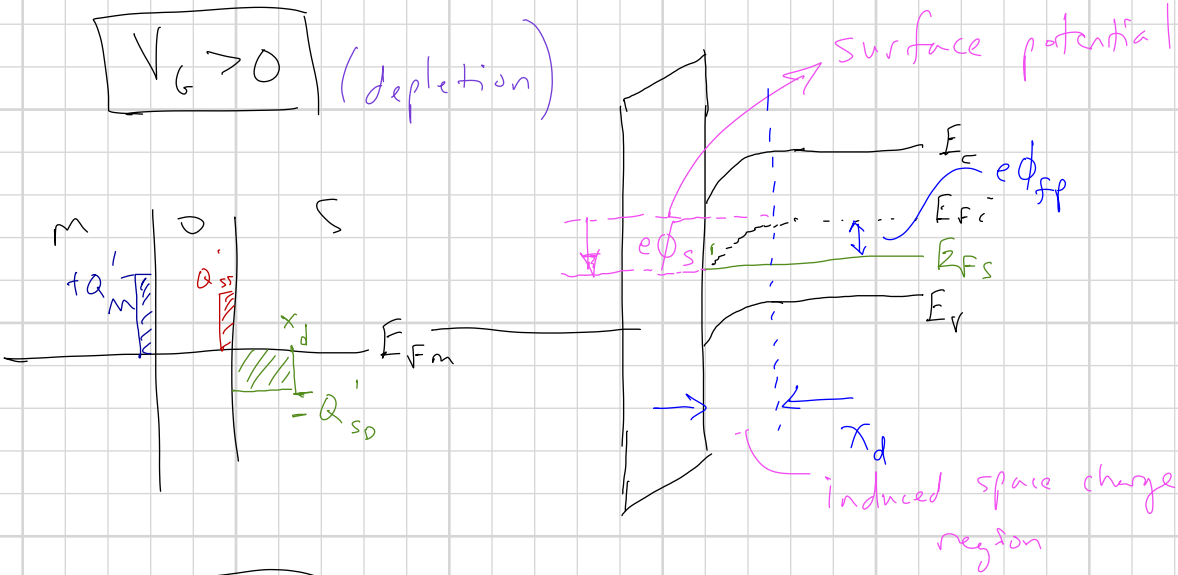
$V_G = V_{FB}$ (flat band)



$V_G < 0$ (accumulation)



$V_G > 0$ (depletion)

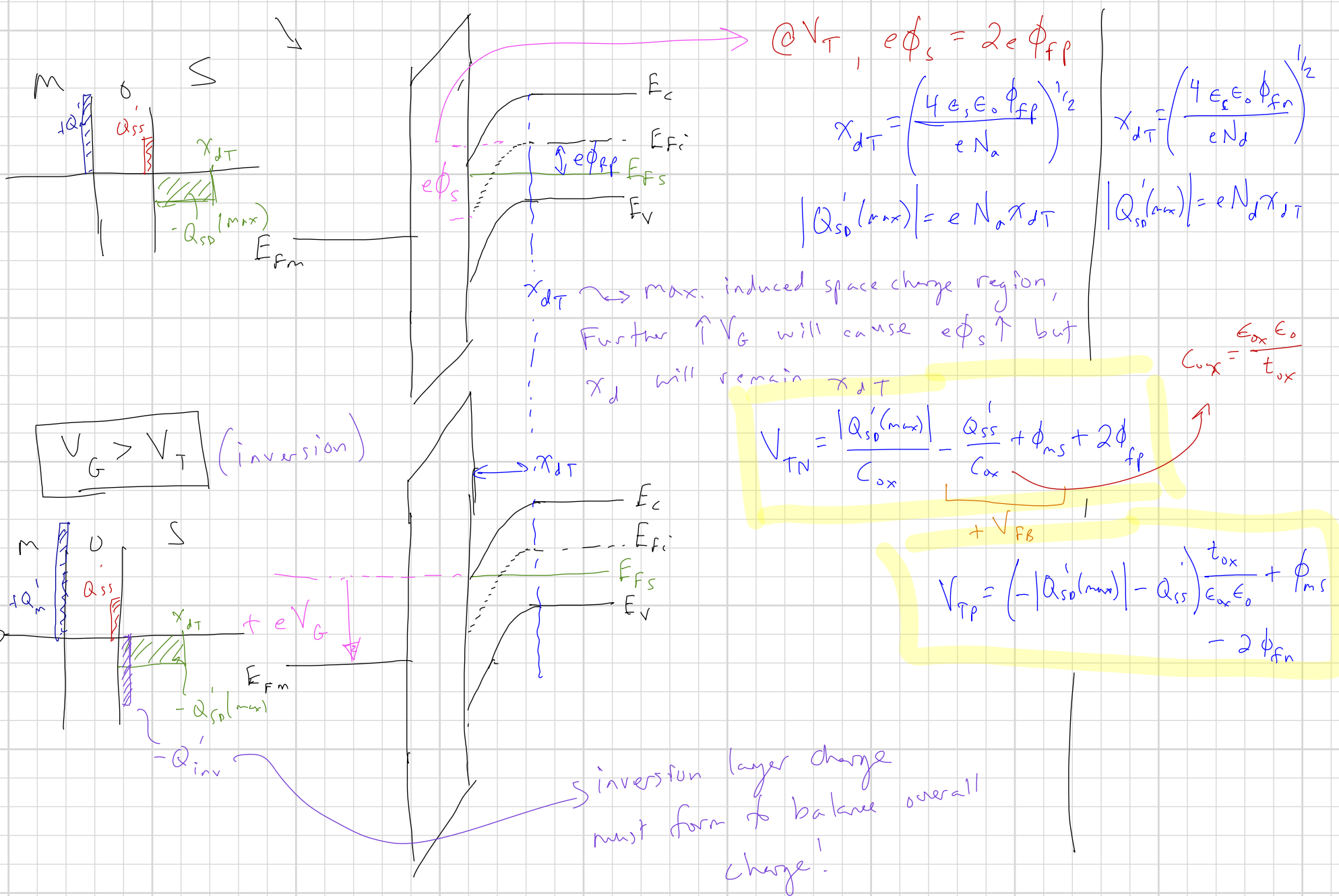


$V_G = V_T$ (threshold inversion)

p-type $\phi_{fp} = V_t \ln\left(\frac{N_a}{n_i}\right)$ n-type $\phi_{fn} = V_t \ln\left(\frac{N_d}{n_i}\right)$
true for all bias conditions

$V_{FB} = \phi_{ms} - \frac{Q_{ss}'}{C_{ox}} \rightarrow \phi_{ms} = \phi_m' - \left(\chi' + \frac{E_g}{2e} - \phi_t\right)$

$\chi_d = \left(\frac{2\epsilon_s\epsilon_0\phi_s}{eN_a}\right)^{1/2}$ $\chi_d = \left(\frac{2\epsilon_s\epsilon_0\phi_s}{eN_d}\right)^{1/2}$
 $e\phi_s = E_{Fi}|_{bulk} - E_{Fi}|_{surface}$



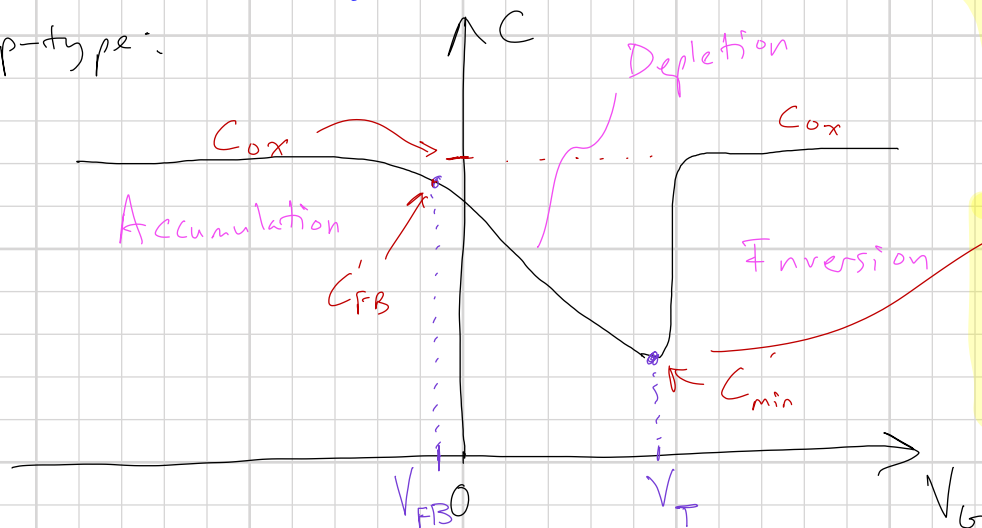
Capacitance is an AC parameter, not DC, thus is measured by adding a small-signal onto an applied DC signal

$$C = \frac{dQ}{dV} \quad \text{change in charge} \quad \text{change in voltage}$$

Ideal C-V

- No oxide trapped charges and no interface states (at oxide-s.c. interface)
- low frequency AC signal

Ex: p-type:



Flat-Band Cap.

$$C'_{FB} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox} + \left(\frac{\epsilon_{ox}}{\epsilon_s} \right) \sqrt{V_t \left(\frac{\epsilon_s \epsilon_0}{e N_a} \right)}}$$

when $x_d = x_{dT}$ ($V_G = V_T$)

$$C'_{min} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox} + \left(\frac{\epsilon_{ox}}{\epsilon_s} \right) x_{dT}}$$